



General Description:

- (1) Chip Dimension
 Chip Size= 13.3 mil x 15.8 mil (340um x 400um)
 Chip Thickness = 90±10μm
 P/N Bonding Pad = 85±5μm
- (2) Electrode:
 P (Anode) → Au
 N (Cathode) → Au
- (3) Structure:
 Refer to drawing
 SiO₂ Passivated surface

Electro-optical Characteristics(Ta=RT)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Condition |
|---------------------|----------------|------|------|------|------|----------------------|
| Forward Voltage | V _F | 2.8 | - | 3.5 | V | I _F =20mA |
| Dominant Wavelength | λ _D | 450 | 460 | 470 | nm | I _F =20mA |
| Reverse Current | I _R | 0 | - | 1 | μA | V _R =-5V |

| Luminous Intensity(I _v) mcd at I _F =20mA | Dominant Wavelength(nm) | | | | | | | | | | | | |
|--|-------------------------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|-----------|
| | Range | 445~447.5 | 447.5~450 | 450~452.5 | 452.5~455 | 455~457.5 | 457.5~460 | 460~462.5 | 462.5~465 | 465~467.5 | 467.5~470 | 470~472.5 | 472.5~475 |
| 70-80 | | | | | | | | | | | | | |
| 80-90 | | | * | * | | | | | | | | | |
| 90-100 | | | * | * | * | | | | | | | | |
| 100-120 | | | | * | * | * | * | * | | | | | |
| 120-140 | | | | * | * | * | * | * | | | | | |
| 140-160 | | | | | * | * | * | * | * | | | | |
| 160-180 | | | | | | * | * | * | * | | | | |
| 180-200 | | | | | | | * | * | * | * | | | |
| 200-240 | | | | | | | | | | | | | |

Features:

- 1. High Luminous Intensity
- 2. Long Operation Life
- 3. High Current; Pulse Operation
- 4. Indoor/Outdoor Applications

Notes:

- 1. Dominant wavelength includes an error of ± 1nm
- 2. Luminous intensity includes an error ±10%
- 3. Luminous intensity is measured on bare chip
- 4. InGaN LED is sensitive to ESD